# 2SD1752, 2SD1752A

### Silicon NPN epitaxial planar type

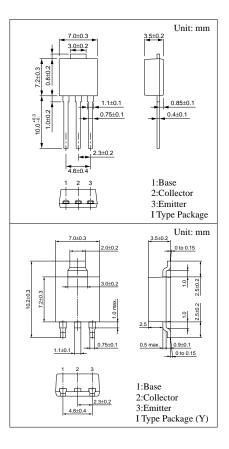
For power amplification and low-voltage switching Complementary to 2SB1148 and 2SB1148A

#### Features

- ullet Low collector to emitter saturation voltage  $V_{\text{CE(sat)}}$
- High-speed switching
- Satisfactory linearity of foward current transfer ratio h<sub>FE</sub>
- Large collector current I<sub>C</sub>
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to	2SD1752	37	40	V	
base voltage	2SD1752A	$V_{CBO}$	50		
Collector to	2SD1752	**	20	V	
emitter voltage	2SD1752A	$V_{CEO}$	40		
Emitter to base voltage		$V_{\rm EBO}$	5	V	
Peak collector current		$I_{CP}$	20	A	
Collector current		$I_{C}$	10	A	
Collector power	T <sub>C</sub> =25°C	D	15	337	
dissipation	Ta=25°C	$P_{C}$	1.3	W	
Junction temperature		$T_{j}$	150	°C	
Storage temperature		$T_{\rm stg}$	-55 to +150	°C	



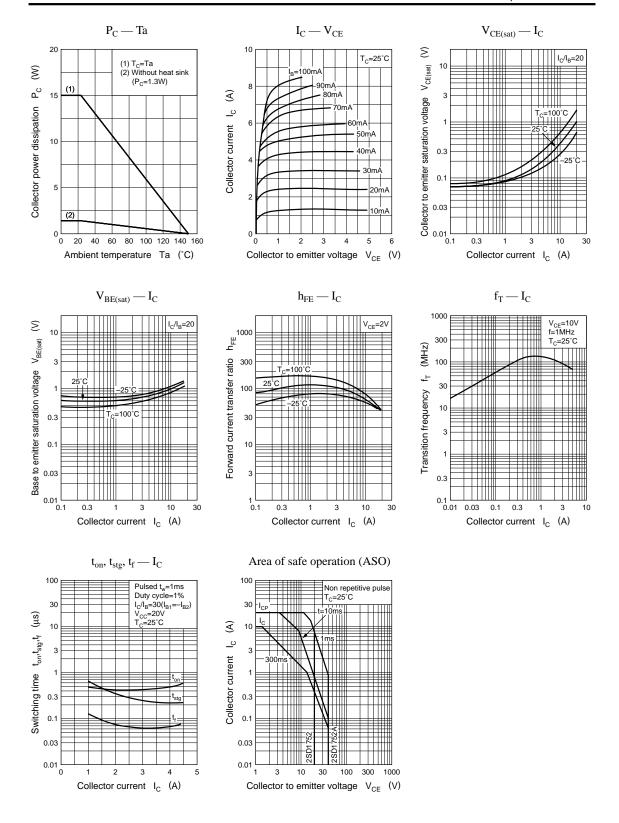
#### Electrical Characteristics (T<sub>C</sub>=25°C)

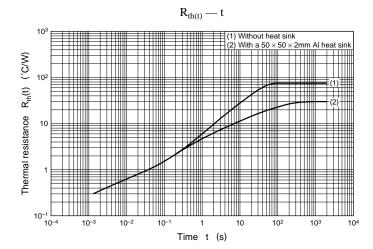
Paramete	er	Symbol	Conditions	min	typ	max	Unit
Collector cutoff	2SD1752	I <sub>CBO</sub>	$V_{CB} = 40V, I_{E} = 0$			50	
current	2SD1752A		$V_{CB} = 50V, I_{E} = 0$			50	μΑ
Emitter cutoff current		I <sub>EBO</sub>	$V_{EB} = 5V, I_C = 0$			50	μА
Collector to emitter	2SD1752	V <sub>CEO</sub>	$I_C = 10\text{mA}, I_B = 0$	20			V
voltage	2SD1752A			40			
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = 2V, I_{C} = 0.1A$	45			
		h <sub>FE2</sub> *	$V_{CE} = 2V$ , $I_C = 3A$	90		260	
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = 10A, I_B = 0.33A$			0.6	V
Base to emitter saturation voltage		V <sub>BE(sat)</sub>	$I_C = 10A, I_B = 0.33A$			1.5	V
Transition frequency		$f_T$	$V_{CE} = 10V, I_{C} = 0.5A, f = 10MHz$		120		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		200		pF
Turn-on time		t <sub>on</sub>	$I_C = 3A$ , $I_{B1} = 0.1A$ , $I_{B2} = -0.1A$ , $V_{CC} = 20V$		0.3		μs
Storage time		t <sub>stg</sub>			0.4		μs
Fall time		t <sub>f</sub>			0.1		μs

#### \*h<sub>FE2</sub> Rank classification

Rank	Q	P
h <sub>FE2</sub>	90 to 180	130 to 260

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